

CLAIM AMENDMENTS:

The following listing replaces all previous listings of the claims:

1. (Currently amended) A semiconductor device, comprising:

a solid state device;

a semiconductor chip having a functional surface on which a functional element is formed, the semiconductor chip being bonded on a surface of the solid state device with the functional surface thereof facing the surface of the solid state device while maintaining a predetermined distance between the functional surface thereof and the surface of the solid state device;

a pillar-shaped connecting member configured to connect the functional surface of the semiconductor chip to the surface of the solid state device and;

an insulating film provided on the surface of the solid state device facing the semiconductor chip, the insulating film having an opening greater in size than the semiconductor chip when the surface of the solid state device facing the semiconductor chip is ~~vertically viewed down in plane~~ from vertically above; and

a sealing layer that seals a space between the solid state device and the semiconductor chip.

2. (Currently amended) [[A]] The semiconductor device according to Claim 1, wherein the sealing layer is provided in such a manner as to fill the opening with the sealing layer.

3. (New) The semiconductor device according to Claim 1, wherein a height of the pillar-shaped connecting member from the surface of the solid state device is approximately equal to a thickness of the insulating film.

4. (New) The semiconductor device according to Claim 1, wherein the pillar-shaped connecting member is formed by bonding a connection pad provided on the solid state device and a projection electrode provided on the semiconductor chip.

5. (New) The semiconductor device according to Claim 1, wherein no other wiring than a connection pad for connection with the semiconductor chip is provided on the solid state device between the solid state device and the semiconductor chip.

6. (New) The semiconductor device according to Claim 1, wherein a distance between an outer periphery of the semiconductor chip and an edge of the opening of the insulating film is 0.1 mm or more when the surface of the solid state device facing the semiconductor chip is viewed from vertically above.

7. (New) The semiconductor device according to Claim 1, wherein the semiconductor chip is connected in a flip chip manner.